

Yuanzhong Zhou

List of Publications by Year in descending order

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30
papers

197
citations

1464605

7
h-index

1255698

13
g-index

30
all docs

30
docs citations

30
times ranked

108
citing authors

#	ARTICLE	IF	CITATIONS
1	Characterization and Modeling of the Transient Safe Operating Area in LDMOS Transistors. , 2019, , .		4
2	Modeling and Simulation of Comprehensive Diode Behavior Under Electrostatic Discharge Stresses. IEEE Transactions on Device and Materials Reliability, 2019, 19, 90-96.	1.5	18
3	Thermal failure and voltage overshoot models for diode behavior under electrostatic discharge stresses. , 2018, , .		1
4	ESD protection structure with reduced capacitance and overshoot voltage for high speed interface applications. Microelectronics Reliability, 2017, 79, 201-205.	0.9	10
5	Compact Thermal Failure Model for Devices Subject to Electrostatic Discharge Stresses. IEEE Transactions on Electron Devices, 2015, 62, 4128-4134.	1.6	17
6	Compact failure modeling for devices subject to electrostatic discharge stresses – A review pertinent to CMOS reliability simulation. Microelectronics Reliability, 2015, 55, 15-23.	0.9	9
7	High-Robustness and Low-Capacitance Silicon-Controlled Rectifier for High-Speed I/O ESD Protection. IEEE Electron Device Letters, 2013, 34, 178-180.	2.2	40
8	vfTLP-VTH: A new method for quantifying the effectiveness of ESD protection for the CDM classification test. Microelectronics Reliability, 2013, 53, 196-204.	0.9	3
9	Investigation on effectiveness of series gate resistor in CDM ESD protection designs. , 2013, , .		4
10	Modeling of high voltage devices for ESD event simulation in SPICE. Microelectronics Journal, 2012, 43, 305-311.	1.1	6
11	Prediction and Modeling of Thin Gate Oxide Breakdown Subject to Arbitrary Transient Stresses. IEEE Transactions on Electron Devices, 2010, 57, 2296-2305.	1.6	16
12	Gate oxide evaluation under very fast transmission line pulse (VFTLP) CDM-type stress. , 2008, , .		12
13	ESD Simulation using Compact Models: from I/O Cell to Full Chip. , 2007, , .		8
14	Compact Modeling of On-Chip ESD Protection Using Standard MOS and BJT Models. , 2006, , .		7
15	Plasma ion implantation hydrogenation of poly-Si CMOS thin-film transistors at low energy and high dose rate using an inductively-coupled plasma source. IEEE Transactions on Electron Devices, 1998, 45, 1324-1328.	1.6	6
16	Fabrication of low dielectric constant materials for ULSI multilevel interconnection by plasma ion implantation. IEEE Electron Device Letters, 1998, 19, 420-422.	2.2	8
17	Plasma Chemistry Study of Plasma Ion Implantation Doping for Cmos Devices. Materials Research Society Symposia Proceedings, 1998, 510, 239.	0.1	1
18	Low-Dielectric Constant SiO(F,C) Films for ULSI Interconnections Prepared by CF4 Plasma Ion Implantation. Materials Research Society Symposia Proceedings, 1998, 511, 63.	0.1	0

#	ARTICLE	IF	CITATIONS
19	Optimizing high efficient plasma immersion ion implantation hydrogenation for poly-Si thin film transistors. Nuclear Instruments & Methods in Physics Research B, 1997, 124, 69-75.	0.6	10
20	Plasma Ion Implantation for Flat Panel Displays. Materials Research Society Symposia Proceedings, 1996, 438, 321.	0.1	2
21	N-Type Doping by Plasma Ion Implantation Using a PH ₃ SDS System. Materials Research Society Symposia Proceedings, 1996, 438, 351.	0.1	4
22	Investigations of Plasma Immersion Ion Implantation Hydrogenation for Poly-Si Tfts Using an Inductively Coupled Plasma Source. Materials Research Society Symposia Proceedings, 1996, 438, 357.	0.1	1
23	Plasma Immersion Ion Implantation Modification of Surface Properties of Polymer Material. Materials Research Society Symposia Proceedings, 1996, 438, 511.	0.1	3
24	Investigations of Plasma Immersion Ion Implantation Hydrogenation for Poly-Si Tfts Using an Inductively Coupled Plasma Source. Materials Research Society Symposia Proceedings, 1996, 439, 269.	0.1	0
25	Nitrogen Plasma Ion Implantation into Carbon Films Deposited by the Anodic Vacuum Arc. Materials Research Society Symposia Proceedings, 1995, 388, 281.	0.1	0
26	Carbon Nitride (C _x N _x) Films Formed by Ion Implantation into Thin Carbon Films. Materials Research Society Symposia Proceedings, 1995, 396, 255.	0.1	3
27	Short-Time Hydrogen Passivation of Poly-Si CMOS Thin film Transistors by High Dose Rate Plasma Ion Implantation. Materials Research Society Symposia Proceedings, 1995, 396, 515.	0.1	4
28	Anodic vacuum arc deposition of carbon and nitrogen containing carbon films. , 0, , .		0
29	Study of high efficient Plasma Immersion Ion Implantation hydrogenation for CMOS poly-Si TFTs using an ICP plasma source. , 0, , .		0
30	Hydrodynamic and analytical models for plasma immersion ion implantation with dielectric substrates. , 0, , .		0